

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, emplo



November 2015

FODM121 Series, FODM124, FODM2701, FODM2705

4-Pin Full Pitch Mini-Flat Package Phototransistor Optocouplers

Features

- More than 5 mm Creepage/Clearance
- Compact 4-Pin Surface Mount Package (2.4 mm Maximum Standoff Height)
- · Current Transfer Ratio in Selected Groups:

DC Input:

FODM121: 50–600% FODM121A: 100–300% FODM121B: 50–150% FODM121C: 100–200% FODM124: 100% MIN FODM2701: 50–300%

AC Input:

FODM2705: 50-300%

- · Safety and Regulatory Approvals:
 - UL1577, 3,750 VAC_{RMS} for 1 Minute
 - DIN-EN/IEC60747-5-5, 565 V Peak Working Insulation Voltage

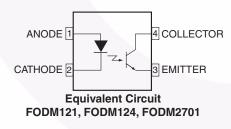
Applications

- Digital Logic Inputs
- Microprocessor Inputs
- Power Supply Monitor
- · Twisted Pair Line Receiver
- Telephone Line Receiver

Description

The FODM121 series, FODM124, and FODM2701 consists of a gallium arsenide infrared emitting diode driving a phototransistor in a compact 4-pin mini-flat package. The lead pitch is 2.54 mm. The FODM2705 consists of two gallium arsenide infrared emitting diodes connected in inverse parallel for AC operation.

Functional Block Diagram



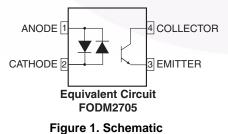




Figure 2. Package Outlines

Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter		Characteristics
Installation Classifications per DIN VDE	< 150 V _{RMS}	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V _{RMS}	I–III
Climatic Classification		40/110/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	904	V _{peak}
V PR	Input-to-Output Test Voltage, Method B, V _{IORM} x 1.875 = V _{PR} , 100% Production Test with t _m = 1 s, Partial Discharge < 5 pC		V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	565	V_{peak}
V_{IOTM}	Highest Allowable Over-Voltage	6000	V_{peak}
	External Creepage	≥ 5	mm
	External Clearance	≥ 5	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
T _S	Case Temperature ⁽¹⁾	150	°C
I _{S,INPUT}	Input Current ⁽¹⁾	200	mA
P _{S,OUTPUT}	Output Power ⁽¹⁾	300	mW
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500 V ⁽¹⁾	> 10 ⁹	Ω

Note:

1. Safety limit values – maximum values allowed in the event of a failure.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A = 25^{\circ}C$ Unless otherwise specified.

Symbol	Parai	Value	Unit	
TOTAL PACK	\GE		1	
T _{STG}	Storage Temperature		-40 to +125	°C
T _{OPR}	Operating Temperature		-40 to +110	°C
T _J	Junction Temperature		-40 to +125	°C
T _{SOL}	Lead Solder Temperature		260 for 10 sec	°C
EMITTER			<u>.</u>	
I _{F (avg)}	Continuous Forward Current		50	mA
I _{F (pk)}	Peak Forward Current (1 µs puls	se, 300 pps.)	1	Α
V _R	Reverse Voltage		6	V
Б	Power Dissipation		70	mW
P_{D}	Derate linearly (Above 75°C)		1.41	mW/°C
DETECTOR				
I _C	Continuous Collector Current		80	mA
M	Collector-Emitter Voltage	FODM121 Series, FODM124	80	V
V_{CEO}		FODM2701, FODM2705	40	V
V _{ECO}	Emitter-Collector Voltage		6	V
Ь	Power Dissipation		150	mW
P_{D}	Derate linearly (Above 80°C)		3.27	mW/°C

Electrical Characteristics

 $T_A = 25$ °C unless otherwise specified.

Symbol	Parameter	Device	Test Conditions	Min.	Тур.	Max.	Unit	
INDIVIDU	AL COMPONENT CHAR	ACTERISTICS						
Emitter								
	_	FODM121 Series, FODM124	I _F = 10 mA	1.0		1.3		
V_{F}	Forward Voltage	FODM2701	$I_F = 5 \text{ mA}$		1	4.4	V	
		FODM2705	$I_F = \pm 5 \text{ mA}$			1.4		
I _R	Reverse Current	FODM121 Series, FODM124, FODM2701	V _R = 5 V			5	μА	
Detector								
DV	Collector-Emitter	FODM121 Series, FODM124	1 2 2 2	80			.,	
BV _{CEO}	Breakdown Voltage	FODM2701, FODM2705	$I_C = 1 \text{ mA}, I_F = 0$	40			V	
BV _{ECO}	Emitter-Collector Breakdown Voltage	All	$I_E = 100 \ \mu A, \ I_F = 0$	7			V	
I _{CEO}	Collector Dark Current	All	$V_{CE} = 40 \text{ V}, I_{F} = 0$			100	nA	
C _{CE}	Capacitance	All	V _{CE} = 0 V, f = 1 MHz		10		pF	
TRANSFE	R CHARACTERISTICS							
		FODM2701	$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	50		300		
		FODM2705	$I_F = \pm 5 \text{ mA}, V_{CE} = 5 \text{ V}$	50		300	%	
		FODM121	5.70 \/ 5.1/	50		600		
CTR	DC Current Transfer	FODM121A		100		300		
CIK	Ratio	FODM121B	$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	50		150		
		FODM121C		100		200		
		FODM404	$I_F = 1 \text{ mA}, V_{CE} = 0.5 \text{ V}$	100		1200		
		FODM124	$I_F = 0.5 \text{ mA}, V_{CE} = 1.5 \text{ V}$	50				
	CTR Symmetry	FODM2705	$I_F = \pm 5 \text{ mA}, V_{CE} = 5 \text{ V}$	0.3		3.0		
		FODM121 Series	$I_F = 8 \text{ mA}, I_C = 2.4 \text{ mA}$			0.4		
V	Caturation Valtage	FODM124 $I_F = 1 \text{ mA}, I_C = 0.5$				0.4	\/	
VCE(SAT)	Saturation Voltage	FODM2701	$I_F = 10 \text{ mA}, I_C = 2 \text{ mA}$			0.3	- V -	
		FODM2705	$I_F = \pm 10 \text{ mA}, I_C = 2 \text{ mA}$			0.3		
t _r	Rise Time (Non-Saturated)	All	I_C = 2 mA, V_{CE} = 5 V, R_L = 100 Ω		3		μs	
t _f	Fall Time (Non-Saturated)	All	I_C = 2 mA, V_{CE} = 5 V, R_L = 100 Ω		3		μs	
ISOLATIC	N CHARACTERISTICS							
V _{ISO}	Steady State Isolation Voltage ⁽²⁾	All	1 minute	3750			VAC _{RMS}	

Note:

2. Steady state isolation voltage, V_{ISO}, is an internal device dielectric breakdown rating. For this test, pins 1 and 2 are common, and pins 3 and 4 are common.

Typical Performance Curves

 $T_A = 25$ °C unless otherwise specified.

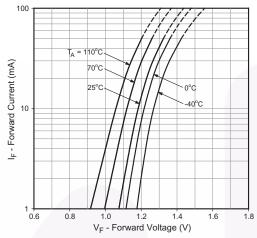


Fig. 3 Forward Current vs. Forward Voltage

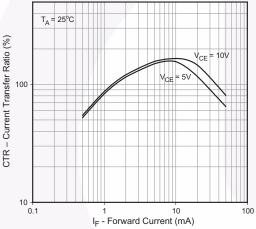


Fig. 5 Current Transfer Ratio vs. Forward Current (FODM121/2701/2705)

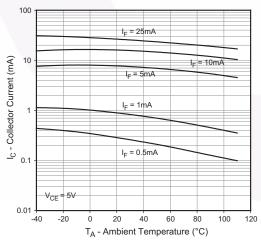


Fig. 7 Collector Current vs. Ambient Temperature (FODM121/2701/2705)

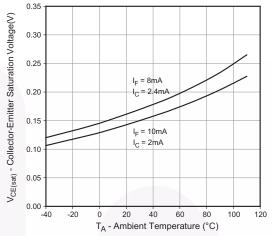


Fig. 4 Collector-Emitter Saturation Voltage vs. Ambient Temperature (FODM121/2701/2705)

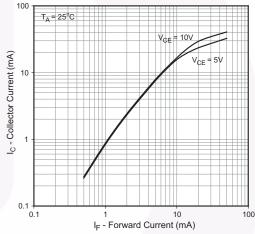


Fig. 6 Collector Current vs. Forward Current (FODM121/2701/2705)

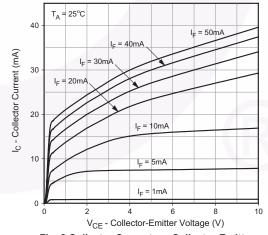


Fig. 8 Collector Current vs. Collector-Emitter Voltage (FODM121/2701/2705)

Typical Performance Curves (Continued)

 $T_A = 25$ °C unless otherwise specified.

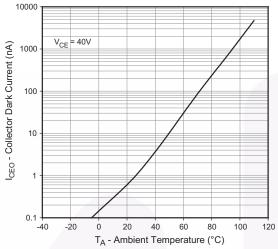


Fig 9. Collector Dark Current vs. Ambient Temperature (FODM121/2701/2705)

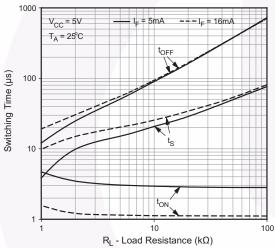


Fig. 11 Switching Time vs. Load Resistance (FODM121/2701/2705)

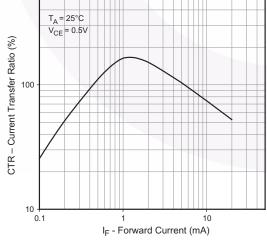


Fig. 13 Current Transfer Ratio vs. Forward Current (FODM124)

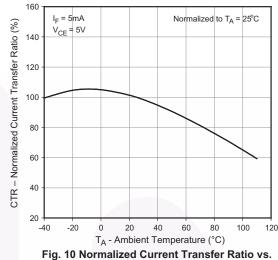


Fig. 10 Normalized Current Transfer Ratio vs. Ambient Temperature (FODM121/2701/2705)

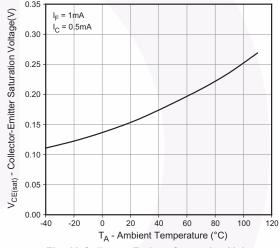


Fig. 12 Collector-Emitter Saturation Voltage vs. Ambient Temperature (FODM124)

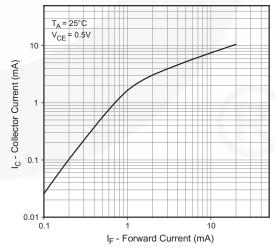


Fig 14. Collector Current vs. Forward Current (FODM124)

Typical Performance Curves (Continued)

 $T_A = 25$ °C unless otherwise specified.

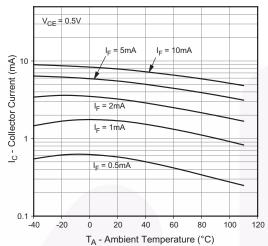


Fig 15. Collector Current vs. Ambient Temperature (FODM124)

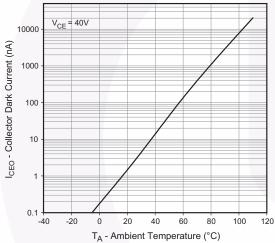


Fig. 17 Collector Dark Current vs. Ambient Temperature (FODM124)

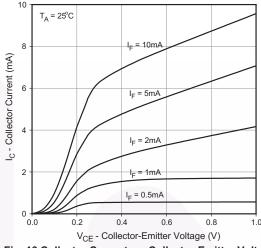


Fig. 16 Collector Current vs. Collector-Emitter Voltage (FODM124)

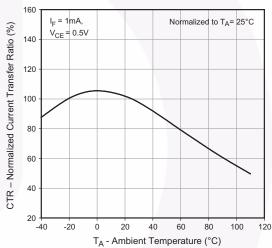


Fig. 18 Normalized Current Transfer Ratio vs.
Ambient Temperature (FODM124)

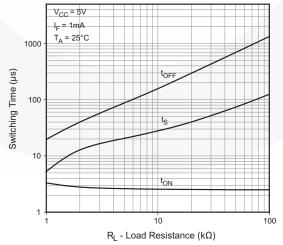
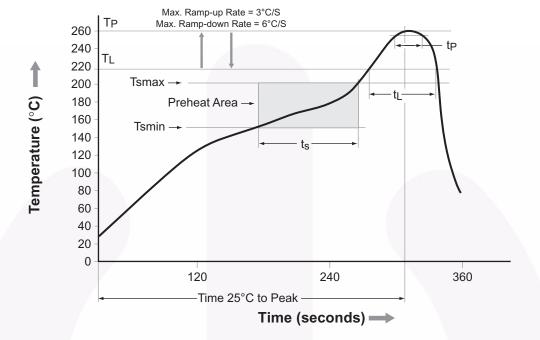


Fig. 19 Switching Time vs. Load Resistance (FODM124)

Reflow Profile



Profile Freature	Pb-Free Assembly Profile	
Temperature Min. (Tsmin)	150°C	
Temperature Max. (Tsmax)	200°C	
Time (t _S) from (Tsmin to Tsmax)	60-120 seconds	
Ramp-up Rate (t _L to t _P)	3°C/second max.	
Liquidous Temperature (T _L)	217°C	
Time (t _L) Maintained Above (T _L)	60-150 seconds	
Peak Body Package Temperature	260°C +0°C / -5°C	
Time (t _P) within 5°C of 260°C	30 seconds	
Ramp-down Rate (T _P to T _L)	6°C/second max.	
Time 25°C to Peak Temperature	8 minutes max.	

Ordering Information

Part Number	Package	Packing Method
FODM121	Full Pitch Mini-Flat 4-Pin	Tube (100 units)
FODM121R2	Full Pitch Mini-Flat 4-Pin	Tape and Reel (2500 Units)
FODM121V	Full Pitch Mini-Flat 4-Pin, DIN EN/IEC60747-5-5 Option	Tube (100 Units)
FODM121R2V	Full Pitch Mini-Flat 4-Pin, DIN EN/IEC60747-5-5 Option	Tape and Reel (2500 Units)

Note:

The product orderable part number system listed in this table also applies to the FODM121A, FODM121B, FODM121C, FODM124, FODM2701, and FODM2705 products.

Marking Information

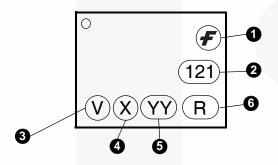
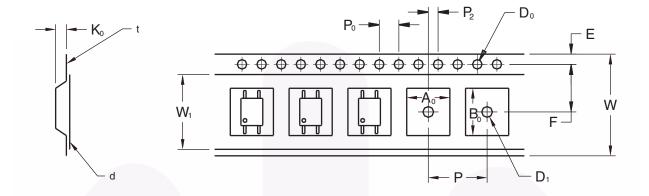


Figure 20. Top Mark

Table 1. Top Mark Definitions

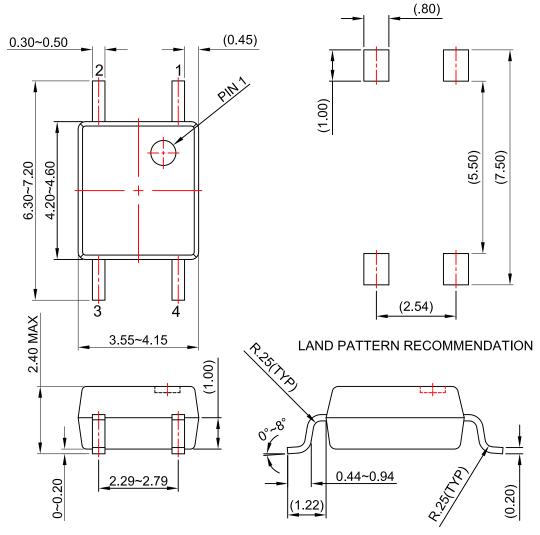
1	Fairchild Logo
2	Device Number
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
4	One-Digit Year Code, e.g., "5"
5	Digit Work Week, Ranging from "01" to "53"
6	Assembly Package Code

Carrier Tape Specifications



		2.54 Pitch
Description	Symbol	Dimensions
Tape Width	W	12.00±0.4
Tape Thickness	t	0.35±0.02
Sprocket Hole Pitch	P ₀	4.00±0.20
Sprocket Hole Dia.	D ₀	1.55±0.20
Sprocket Hole Location	E	1.75±0.20
Pocket Location	F	5.50±0.20
	P ₂	2.00±0.20
Pocket Pitch	Р	8.00±0.20
Pocket Dimension	A ₀	4.75±0.20
	B ₀	7.30±0.20
	K ₀	2.30±0.20
Pocket Hole Dia.	D ₁	1.55±0.20
Cover Tape Width	W ₁	9.20
Cover Tape Thickness	d	0.065±0.02
Max. Component Rotation or Tilt		20° max
Devices Per Reel		2500
Reel Diameter		330 mm (13")

2 E4 Ditab



NOTES:

- A) NO STANDARD APPLIES TO THIS PACKAGE.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSION
- D) DRAWING FILENAME AND REVISION: MKT-MFP04Crev3.



ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and h

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative